NSN 5961-01-211-2643

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Thyristor Semiconductor Device - Page 1 of 1



View Online at https://aerobasegroup.com/nsn/5961-01-211-2643 **Inclosure Material:** Metal **Overall Length:** 3.622 inches **Overall Height:** 1.417 inches **Overall Width:** 0.787 inches **Internal Configuration:** Junction contact **Mounting Method:** Press fit **Features Provided:** Hermetically sealed case **Semiconductor Material:** Silicon **Voltage Rating In Volts Per Characteristic:** 1300.0 nonrepetitive peak reverse voltage and 1200.0 repetitive peak reverse voltage **Current Rating Per Characteristic:** 90.00 amperes forward current, total rms universal and 145.00 amperes forward current, total rms torr and 160.00 amperes repetitive peak forward current peak **Maximum Operating Tempurature Per Measurement Point:** 125.0 degrees celsius junction **Special Features:** Junction pattern arrangement: pnpn **Terminal Type And Quantity:** 3 binding post Shelf Life: N/a **Unit Of Measure: Demilitarization:** No Fiig: